IN THE CLAIMS:

Please amend the claims as follows:

1. (**Currently Amended**) A method for preparing an oxide thin film on a substrate, comprising: ~~which comprises the steps of~~

admixing a raw gas obtained through ~~the~~ vaporization of a raw material comprising metal atoms for the oxide thin film, a carrier gas and an oxidation gas in a gas-mixing unit; [[,]]

passing the gas mixture through a gas activating means which is arranged between the gas-mixing unit and a shower plate[[,]] and which has a pipe line with An inner wall surface area within a range of 4.8×10^{-3} m^2 to 1.28×10^{-1} m^2, ~~maintaining~~ the gas activating means being maintained at a temperature that induces vapor phase decomposition~~, decomposing the gas mixture into metal atom-containing molecules in the gas activating means~~; and

supplying the gas mixture on a heated substrate placed in a reaction chamber as a chemical vapor phase growth apparatus through the shower plate to ~~thus~~ make the gas mixture react with one another,

wherein a rate of oxidation gas flow rate is not less than 60% on the basis of the gas mixture.

2. (**Withdrawn**) A method for preparing an oxide thin film on a substrate, which comprises the steps of admixing a raw gas obtained through the vaporization of a raw material for the oxide thin film, a carrier gas and an oxidation gas in a gas-mixing unit and supplying the resulting gas mixture on a heated substrate placed in a reaction

chamber as a chemical vapor phase growth apparatus through a shower plate to thus make the gas mixture react with one another, wherein the method comprises the steps of forming an initial layer as a seed layer using the gas mixture and then forming a second layer using the gas mixture containing oxidation gas in a flow rate higher than the oxidation gas flow rate used for forming the initial layer, in succession.

3. (**Withdrawn**) The method for preparing an oxide thin film as set forth in claim 2, wherein the flow rate of oxidation gas used in a film-forming process for forming the initial layer is less than 60%, and the flow rate of oxidation gas used in a film-forming process for forming the second layer is not less than 60%.

Claims 4 and 5 (**Cancelled**).

6. (**Previously Presented**) The method for preparing an oxide thin film as set forth in claim 1, wherein the gas activating means is maintained at a temperature ranging from a temperature without causing any liquefaction or deposition of the raw gas to a temperature without causing film -formation thereof.

7. (**Previously Presented**) The method for preparing an oxide thin film as set forth in claim 1, wherein the oxidation gas is a member selected from the group consisting of oxygen, ozone, N_2O and NO_2.

8. (**Previously Presented**) The method for preparing an oxide thin film as set forth in claim 1, wherein the carrier gas used is an inert gas selected from the group consisting of nitrogen, helium, argon, neon and krypton.

9. (**Previously Presented**) The method for preparing an oxide thin film as set forth in claim 1, wherein the substrate used is one prepared from a material selected from the group consisting of Pt, Ir, Rh, Ru, MgO, $SrTiO_3$, IrO_2, RuO_2, $SrRuO_3$, and $LaNiO_3$.

10. (**Currently Amended**) The method for preparing an oxide thin film as set forth in claim 1, wherein the oxide thin film is ~~made from~~ constituted of an oxide of a paraelectric dielectric material selected from the group consisting of SiO_2, TiO_2, Al_2O_3, Ta_2O_5, MgO, ZrO_2, HfO_2, (Ba, Sr)TiO_2 and $SrTiO_3$; or an oxide of a ferroelectric material selected from the group consisting of Pb(Zr, Ti)O_3, $SrBi_2Ta_2O_9$ and $Bi_4Ti_3O_{12}$.

11. (**Withdrawn**) The method for preparing an oxide thin film as set forth in claim 2, wherein, when a prescribed atom present in the oxide thin film prepared easily diffuse into the substrate, an epitaxial growth is realized by increasing an amount of the atom in the initial layer to a level higher than the atom amount used in the case of the substrate into which the atom hardly diffuses.

12. (**Withdrawn**) An apparatus for preparing an oxide thin film on a substrate by admixing a raw gas obtained through the vaporization of a raw material for the oxide thin film, a carrier gas and an oxidation gas in a gas-mixing unit and supplying the resulting gas mixture on a heated substrate placed in a reaction chamber as a chemical vapor phase growth apparatus through a shower plate to thus make the gas mixture react with one another, wherein a gas activating means is arranged between the gas-mixing unit and the shower plate.

13. (**Withdrawn**) The apparatus for preparing an oxide thin film as set forth in claim 12, wherein the gas activating means is equipped with a heating means.

14. (**Withdrawn**) The apparatus for preparing an oxide thin film as set forth in claim 12, wherein the gas activating means is a pipe line between the gas-mixing unit and the shower plate.

15. (**Withdrawn**) The apparatus for preparing an oxide thin film as set forth in claim 13, wherein the gas activating means is a pipe line between the gas-mixing unit and the shower plate

16. (**Previously Presented**) The method for preparing an oxide thin film as set forth in claim 1, wherein the gas activating means comprises a pipe line equipped with a heating means.